

**Notice of References Cited**

Application/Control No.

09/893,035

Applicant(s)/Patent Under  
Reexamination  
CHO, HAG-JU

Examiner

Erik Kielin

Art Unit

2813

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kukli et al. "In situ study of atomic layer epitaxy growth of tantalum oxide thin films from Ta(OC <sub>2</sub> H <sub>5</sub> ) <sub>5</sub> and H <sub>2</sub> O" Applied Surface Science 112 (1997) pp. 236-242. ✓
	V	Haukka et al. "Growth mechanisms of mixed oxides on alumina" Applied Surface Science 112 (1997) pp. 23-29. ✓
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.